

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/789,042
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2815
Examiner Name	Landau, Matthew

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Attorney Docket No: 1303.050US2

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Examiner Name	Landau, Matthew

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	Group Art Unit	2815
	Examiner Name	Landau, Matthew
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